

AMENDMENTS**In the Specification:**

Please amend the specification as noted below.

Please delete the paragraph on page 8, lines 18 to 19. The paragraph located on page 8, lines 18 to 19 is being deleted in favor of the paragraph located on page 6, lines 28 to 29.

In the Drawings:

Filed concurrently herewith is a Formal Request for Approval of Drawing Changes seeking the following corrections:

In Figure 10, the correction of the spelling of the word "optional".

In the Abstract:

Please replace the current Abstract with the one shown below.

a' --Numerous methods for forming various semiconductor structures are disclosed. In one embodiment, a layered dielectric structure of alternating sub-layers of a first dielectric material and a second dielectric material is formed on a suitable semiconductor substrate. In this embodiment, the layered dielectric structure comprises an alternating pattern of at least two sub-layers of a first dielectric material which is a high-K dielectric material and at least one layer of a second dielectric material which is a standard-K dielectric material, wherein at least one of the one or more second dielectric material sub-layers contain nitrogen implanted therein using a nitridation step.--